



#### 100V NPN MEDIUM POWER LOW SATURATION TRANSISTOR POWERDI®5

#### **Features**

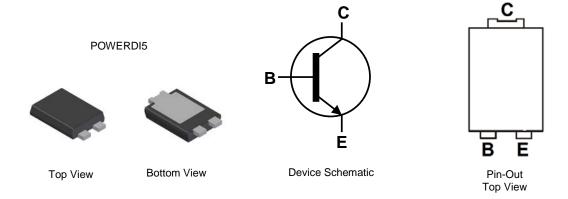
- BV<sub>CEO</sub> > 100V
- I<sub>C</sub> = 6A High Continuous Collector Current
- I<sub>CM</sub> = 10A Peak Collector Current
- P<sub>D</sub> up to 3.2W
- 43% smaller than SOT223; 60% smaller than TO252
- Maximum height just 1.1mm
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: PowerDI5
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.093 grams (approximate)

### **Applications**

- Motor Drive
- Voltage Regulator using Emitter-Follower
- DC-DC Converter
- Telecoms
- **Power Management**



#### **Ordering Information (Note 4)**

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXT2011P5-13	AEC-Q101	DXT2011	13	16	5,000

Notes:

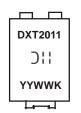
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

1 of 7

www.diodes.com

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



DXT2011 = Product Type Marking Code The Manufacturers' Code Marking K = Factory Designator YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 09 for 2009) WW = Week code (01 to 53)





# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	6	А
Peak Pulse Current	I <sub>CM</sub>	10	Α

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit			
	(Note 5)		3.2			
Power Dissipation	(Note 6)	$P_{D}$	1.7	W		
	(Note 7)		0.74	]		
	(Note 5)		39			
Thermal Resistance, Junction to Ambient Air	(Note 6) R <sub>0JA</sub>	$R_{ heta JA}$	75	0000		
	(Note 7)		169	°C/W		
Thermal Resistance, Junction to Leads (Note 8)		$R_{ heta JL}$	5.6			
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C			

## ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

  6. Same as note (5), except mounted on 25mm x 25mm 1oz copper.

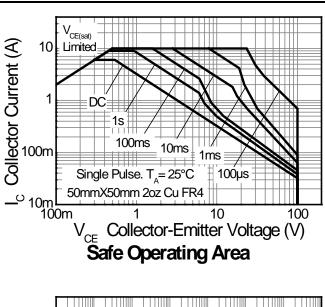
  7. Same as note (5), except mounted on minimum recommended pad (MRP) layout.

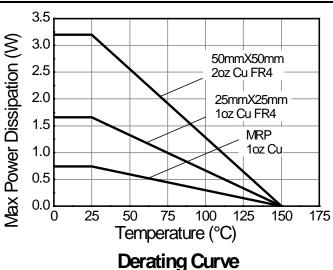
  8. Thermal resistance from junction to solder-point (on the exposed collector pad).

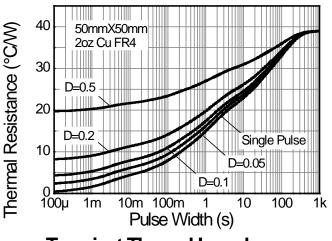
  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

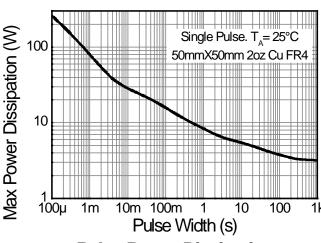


## Thermal Characteristics and Derating Information





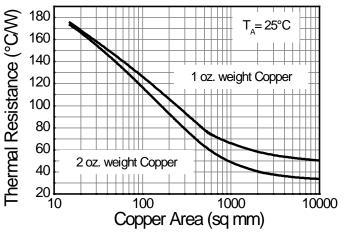


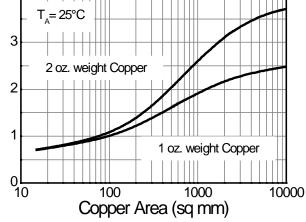


# **Transient Thermal Impedance**

S Power Rating (W)

**Pulse Power Dissipation** 





Thermal Resistance vs. Cu Area

Power Rating vs. Cu Area





**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

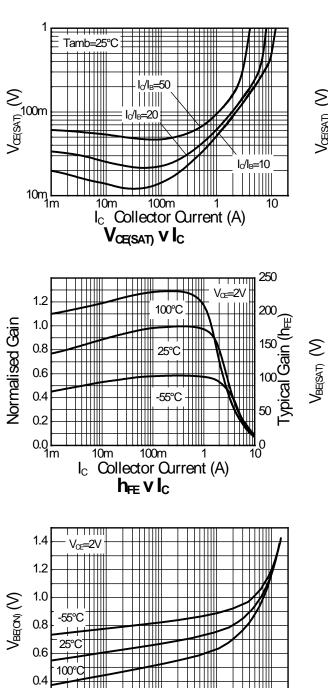
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	200	235	_	>	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	100	115	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.1	_	V	$I_E = 100 \mu A$
Collector Cutoff Current	I <sub>CBO</sub>	1 1	_	20 0.5	nΑ μΑ	V <sub>CB</sub> = 150V V <sub>CB</sub> = 150V, T <sub>AMB</sub> = 100°C
Collector Cutoff Current	I <sub>CER</sub> R≤1kΩ		_ _	20 0.5	nΑ μΑ	V <sub>CB</sub> = 150V V <sub>CB</sub> = 150V, T <sub>AMB</sub> = 100°C
Emitter Cutoff Current	I <sub>EBO</sub>	_		10	nA	V <sub>EB</sub> = 6V
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>	_ _ _	21 50 95 180	35 65 125 220	mV	$I_C = 0.1A$ , $I_B = -5mA$ $I_C = 1A$ , $I_B = 100mA$ $I_C = 2A$ , $I_B = 100mA$ $I_C = 5A$ , $I_B = 500mA$
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	_	1020	1120	mV	$I_C = 5A$ , $I_B = 500mA$
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	_	920	1000	mV	$V_{CE} = 2V$ , $I_C = 5A$
DC Current Gain (Note 10)	h <sub>FE</sub>	100 100 30 10	_ _ _	300 — —	_	V <sub>CE</sub> = 2V, I <sub>C</sub> = 10mA V <sub>CE</sub> = 2V, I <sub>C</sub> = 2A V <sub>CE</sub> = 2V, I <sub>C</sub> = 5A V <sub>CE</sub> = 2V, I <sub>C</sub> = 10A
Transition Frequency	f <sub>T</sub>	1	130	_	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 100mA, f = 50MHz
Output Capacitance	C <sub>obo</sub>		26	_	pF	V <sub>CB</sub> = 10V, f = 1MHz
Switching Times	t <sub>on</sub> t <sub>off</sub>	_ _	41 1010	_ _	ns	$V_{CC} = 10V, I_C = 1A,$ $I_{B1} = I_{B2} = 100mA$

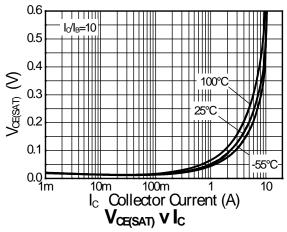
Note: 10. Pulse Test: Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2.0%.

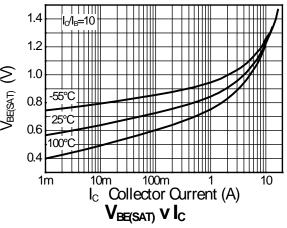




### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



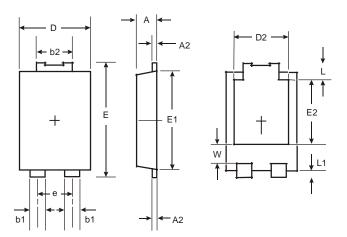






## **Package Outline Dimensions**

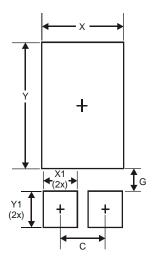
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



POWERDI5					
Dim	Min	Max			
Α	1.05	1.15			
A2	0.33	0.43			
b1	0.80	0.99			
b2	1.70	1.88			
D	3.90	4.05			
D2	3.054 Typ				
Е	6.40	6.60			
е	1.84 Typ				
E1	5.30	5.45			
E2	3.549 Typ				
L	0.75 0.95				
L1	0.50	0.65			
W	1.10 1.41				
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	1.840
G	0.852
Х	3.360
X1	1.390
Υ	4.860
Y1	1.400

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.





#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND. EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT. INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2014, Diodes Incorporated

www.diodes.com